Single Bipolar Transistor multicomp PRO





RoHS Compliant

Absolute Maximum Ratings

Description	Symbol	BD175 BD176	BD177 BD178	BD180	Unit	
Collector Emitter Voltage	Vceo	45	60	80	v	
Collector -Base Voltage	Vсво	45				
Emitter Base Voltage	VEBO	5				
Collector Current	lc	3			_	
Collector Peak Current	Ісм	7			Α	
Power Dissipation @ T _a =25°C Derate above 25°C	PD	1.25 10			W mW/°C	
Power Dissipation @ T₀=25°C]	30			W	
Operating and Storage Junction Temperature Range	Tj, Tstg	-65 to 150			°C	

Electrical Characteristics (Tc = 25°C Unless otherwise specified)

Description	Symbol	Test Condition		Min.	Max.	Unit
Collector Cut-off Current	Ісво	Vcb=45V, IE=0 Vcb=60V, IE=0 Vcb=80V, IE=0	BD175/76 BD177/78 BD180		100	μΑ
Emitter Cut off Current	ІЕВО	V _{EB} =5V, I _C =0			1	mA
Collector Emitter Sustaining Voltag	*VCEO(sus)	IC=100mA, IB=0	BD175/76 BD177/78 BD180	45 60 80		V
Collector Emitter Saturation Voltage	*VCE(sat)	Ic=1A, Iв=0.1A			0.8	
Base Emitter on Voltage	*VBE (on)	Ic=1A, VcE=2V			1.3	
DC Current Gain	*hFE *hFE Group	IC=150mA, VCE=2V IC=1A, VCE=2V IC=150mA, VCE=2V Only BD175/76		-6 -10 -16	40 15 40 63 100	100 160 250
Transition Frequency	f⊤	Ic=250mA, VcE=10V			3	MHz

^{*}Pulse test:- Pulse width=300ms, Duty cycle=1.5%

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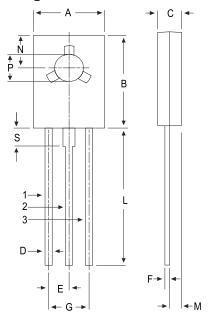


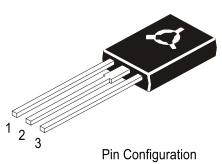
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Thermal Characteristics

Description	Symbol	Value	Unit	
Junction to Ambient in free air	Rth (j-a)	100	°C/W	
Junction to Case	Rth (j-c)	4.16		

Diagram





- 1. Emitter
- 2. Collector
- 3. Base

DIM	MIN	MAX	
Α	7.4	7.8	
В	10.5	10.8	
С	2.4	2.7	
D	0.7	0.9	
Е	2.25 TYP.		
F	0.49	0.75	
G	4.5 TYP.		
L	15.7 TYP.		
М	1.27 TYP.		
N	3.75 TYP.		
Р	3	3.2	
S	2.5 TYP.		

Part Number Table

Description	Part Number	
Single Bipolar Transistor, NPN, 45V, 3000mA, 30W, TO-126	BD175	
Single Bipolar Transistor, PNP, 45V, 3000mA, 30W, TO-126	BD176	
Single Bipolar Transistor, NPN, 60V, 3000mA, 30W, TO-126	BD177	
Single Bipolar Transistor, PNP, 60V, 3000mA, 30W, TO-126	BD178	
Single Bipolar Transistor, PNP, 80V, 3000mA, 30W, TO-126	BD180	

Dimensions: Millimetres

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